

Device	Parameter	Units	Measured/ Extracted	Theoretical	% Error
[2a]	R_{sq}	Ω/\square	0.93	10	
[2a]	N_D	cm^{-3}	10^{21}	10^{21}	0
[2b]	R_{sq}	Ω/\square	0.61	20	
[17a]	Contact R_C	Ω	8.54	224	
[17b]	Contact R_C	Ω	1.46	1760	
[2c]	Resistance R	Ω	91.2	12500	
[2c]	Contact R_C	Ω	10.88	224	
[2d]	Resistance R	Ω	370	1970	
[2d]	Contact R_C	Ω	51.45	1760	
[3]	Field t_{OX}	nm	1150	477.2	
[3]	Field V_T	V	N/A	N/A	N/A
[4]	Gate C_{FB}	F/cm^2	19.3×10^{-9}	3.99×10^{-8}	
[4]	Gate C_{MIN}	F/cm^2	7.74×10^{-9}	N/A	N/A
[4]	Gate V_T	V	-0.26	0.03	
[4]	Gate V_{FB}	V	5.5	-0.84	
[4]	Gate t_{OX}	nm	88	86.5	
[7]	Turn-on V	V	70	N/A	N/A
[8]	ΔL	μm	0.453	3.76	
[9]	ΔW	μm	-8.33	-2.76	
[10]	V_T	V	-4.92	0.03	
[10]	Body effect γ	$\text{V}^{1/2}$	0.910	0.53	
[10]	N_A	cm^{-3}	9.49×10^{24}	8×10^{14}	
[10]	Low-field μ	$\text{cm}^2/(\text{V}\cdot\text{s})$?	?	?